

Inchange Semiconductor

Product Specification

Silicon PNP Power Transistors

MJ4502

DESCRIPTION

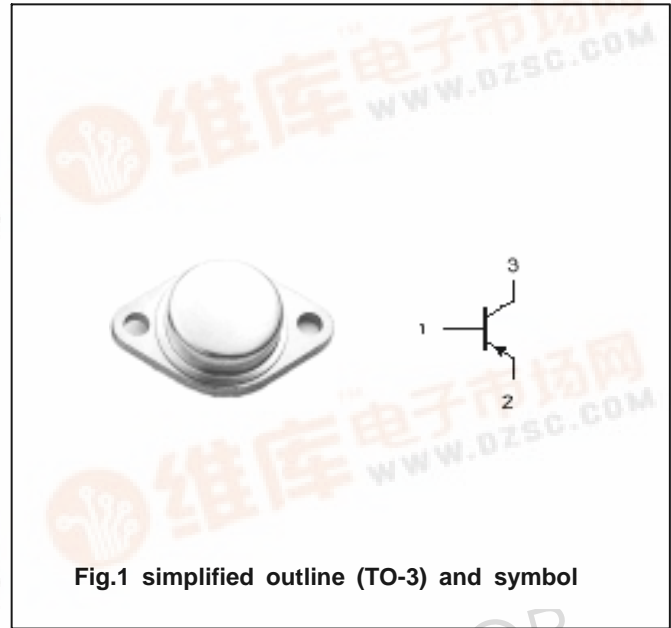
- With TO-3 package
- Complement to type MJ802
- Excellent safe operating area

APPLICATIONS

- For use as an output device in complementary audio amplifiers to 100-Watts music power per channel

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta=)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-100	V
V _{CEO}	Collector-emitter voltage	Open base	-90	V
V _{EBO}	Emitter-base voltage	Open collector	-4	V
I _C	Collector current		-30	A
I _B	Base current		-7.5	A
P _C	Collector power dissipation	T _C =25	200	W
T _j	Junction temperature		200	
T _{stg}	Storage temperature		-65~200	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance junction to case	0.875	/W

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =-0.2A ; I _B =0	-90			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-7.5A; I _B =-0.75A			-0.8	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-7.5A; I _B =-0.75A			-1.3	V
V _{BE}	Base-emitter on voltage	I _C =-7.5A ; V _{CE} =-2V			-1.3	V
I _{CBO}	Collector cut-off current	V _{CB} =-100V; I _E =0 T _C =150			-1.0 -5.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-4V; I _C =0			-1.0	mA
h _{FE}	DC current gain	I _C =-7.5A ; V _{CE} =-2V	25		100	
f _T	Transition frequency	I _C =-1A ; V _{CE} =-10V; f=1.0MHz	2.0			MHz

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PACKAGE OUTLINE

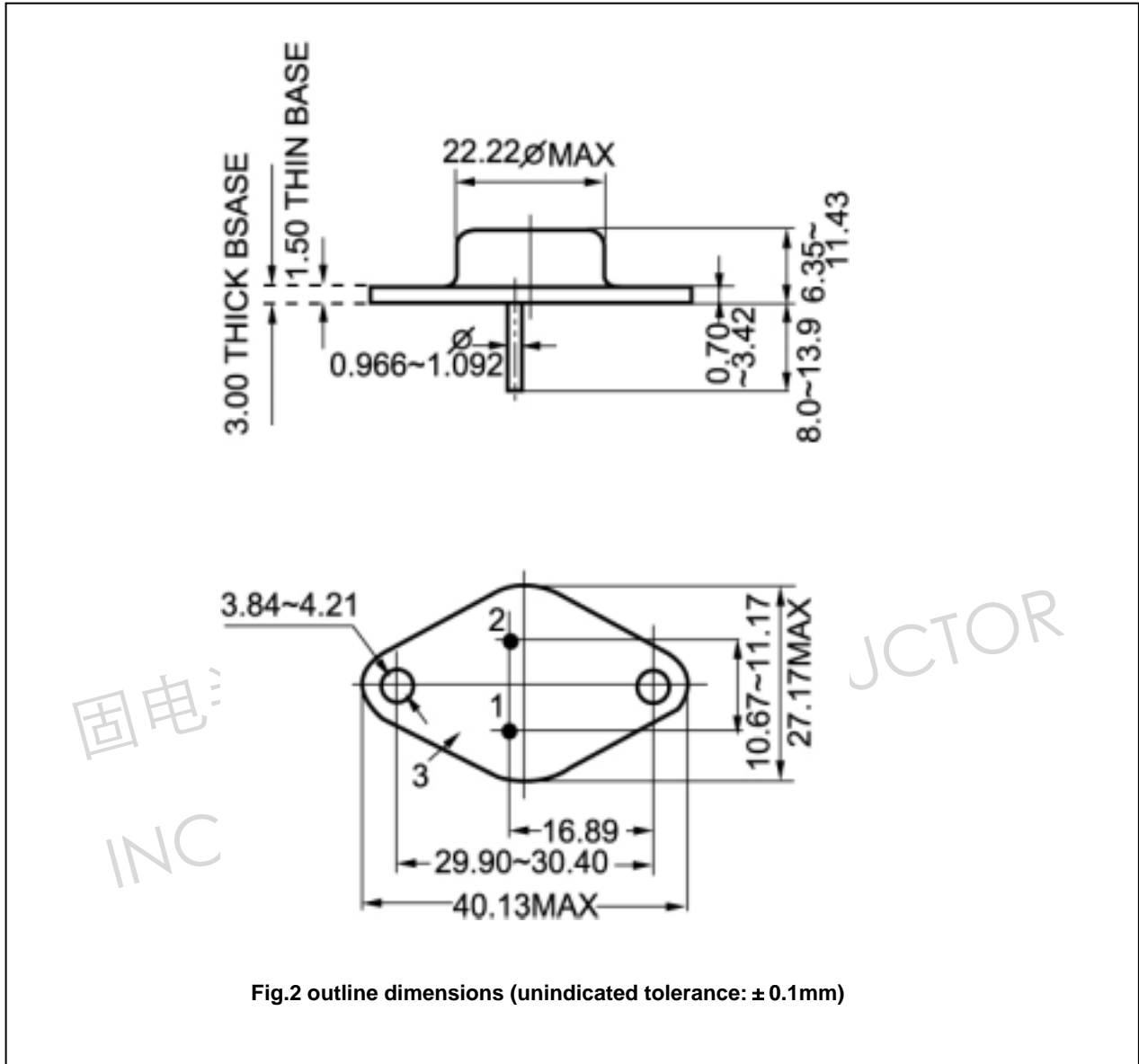


Fig.2 outline dimensions (unindicated tolerance: ± 0.1mm)